## **Tofig Mammadov**

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/2438758/publications.pdf

Version: 2024-02-01

623734 713466 47 571 14 21 citations g-index h-index papers 47 47 47 142 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Deformation effects in electronic spectra of the layered semiconductors TlGaS2, TlGaSe2and TlInS2. Journal of Physics Condensed Matter, 2003, 15, 1291-1298.	1.8	32
2	Memory effect in ferroelectric-semiconductor with incommensurate phase TlGaSe2. Solid State Communications, 2003, 128, 25-28.	1.9	31
3	Anomalous behaviour of the Urbach edge and phase transitions in TlGaSe2. Solid State Communications, 1986, 58, 295-297.	1.9	28
4	Behavior of the layered crystals TlInS2 and TlGaSe2 near phase transitions in a static electric field. Low Temperature Physics, 2000, 26, 56-61.	0.6	28
5	The effect of impurities on the phase transitions in the ferroelectric semiconductors TllnS2and TlGaSe2. Journal of Physics Condensed Matter, 2005, 17, 1985-1993.	1.8	28
6	Phase transition and anisotropy of thermal expansion in TlInS2. Solid State Communications, 1985, 53, 601-602.	1.9	24
7	Dielectric susceptibility behaviour in the incommensurate phase of TllnS2. Physica B: Condensed Matter, 2003, 334, 13-20.	2.7	23
8	Phase transitions and metastable states in TlGaSe2. Phase Transitions, 2003, 76, 1057-1064.	1.3	22
9	Neutron diffraction study of the crystal structure of TllnSe <sub>2</sub> at high pressure. International Journal of Modern Physics B, 2019, 33, 1950149.	2.0	19
10	Structural phase transitions in Fe3+ -doped ferroelectric TlGaSe2 crystal. Solid State Communications, 2008, 145, 539-544.	1.9	18
11	High Pressure Raman Study of Layered Semiconductor Tlgase <sub>2</sub> . Materials Science-Poland, 2018, 36, 203-208.	1.0	18
12	Negative thermal expansion in the layered semiconductor TlGaSe2. Physica Status Solidi (B): Basic Research, 2005, 242, 983-989.	1.5	17
13	The Fundamental Absorption Edge of TllnSe <sub>2</sub> . Physica Status Solidi (B): Basic Research, 1982, 113, K43.	1.5	16
14	Influence of Hydrostatic Pressure on the Fundamental Absorption Edge of TlGaSe <sub>2</sub> , TlGaS <sub>2</sub> , and TllnS <sub>2</sub> Crystals. Physica Status Solidi (B): Basic Research, 1985, 131, K23.	1.5	16
15	Thermal expansion of single crystals of the layered compounds TlGaSe2 and TlInS2. Low Temperature Physics, 2001, 27, 676-680.	0.6	16
16	The Influence of Hydrostatic Pressure on the Fundamental Absorption Edge of Crystals with TlSe‶ype Structure. Physica Status Solidi (B): Basic Research, 1984, 126, K139.	1.5	14
17	Time relaxation of dielectric constant in the commensurate phase of TlGaSe2. Solid State Communications, 2004, 129, 761-764.	1.9	14
18	EPR spectra of Fe3+ centers in layered TlGaSe2 single crystal. Solid State Communications, 2005, 133, 389-392.	1.9	14

#	Article	IF	CITATIONS
19	Effect of illumination on negative linear expansion of TlGaSe2 layered crystals. Journal of Physics and Chemistry of Solids, 2008, 69, 2544-2547.	4.0	13
20	Effect of external fields on the memory effect of the incommensurate phase in the ferroelectric-semiconductor TlGaSe2. Physics of the Solid State, 2008, 50, 108-117.	0.6	13
21	Photodielectric effect in TllnS2 activated by the La impurity. Physics of the Solid State, 2009, 51, 264-269.	0.6	13
22	Identification of intrinsic deep level defects responsible for electret behavior in TlGaSe2 layered semiconductor. Physica B: Condensed Matter, 2016, 483, 82-89.	2.7	13
23	Photoelectric activity of structural defects of a single crystal of the ferroelectric-semiconductor TllnS2: La. Physics of the Solid State, 2014, 56, 1605-1609.	0.6	12
24	The Fundamental Absorption Spectra of Tiinse < sub>2 < /sub> Crystals Under Pressure. Physica Status Solidi (B): Basic Research, 1983, 117, K109.	1.5	9
25	Band Gap Variation in Mixed Crystals with TlSeâ€Type Crystal Structure. Physica Status Solidi (B): Basic Research, 1988, 147, K99.	1.5	9
26	Preparation, crystal structure, and electrical properties of thallium monosulfide in the vicinity of high-temperature phase transitions. Physics of the Solid State, 2006, 48, 2322-2327.	0.6	9
27	Unusual memory effects in an incommensurate phase of the TlInS2 ferroelectric semiconductor. Physics of the Solid State, 2009, 51, 568-576.	0.6	9
28	Thermal history and dielectric behavior in the incommensurate phase of TlGaSe2. Journal of Non-Crystalline Solids, 2005, 351, 2809-2812.	3.1	8
29	Pyroelectric properties and structural defects of a layered TllnS2 crystal doped with lanthanum. Physics of the Solid State, 2014, 56, 2028-2034.	0.6	8
30	Fundamental Absorption Edge of TISe and TIInTe <sub>2</sub> Crystals. Physica Status Solidi (B): Basic Research, 1985, 127, K55.	1.5	7
31	Phase transitions and polytypes in $\hat{l}^2$ TllnS2ferroelectric-semiconductor. Ferroelectrics, Letters Section, 1988, 8, 125-133.	1.0	7
32	Magnetic properties of Co implanted TllnS2 and TlGaSe2 crystals. Solid State Communications, 2012, 152, 407-409.	1.9	7
33	Photoelectric activity of defects in La-doped layered TllnS2 crystals. Low Temperature Physics, 2014, 40, 830-836.	0.6	7
34	Shift of the Fundamental Absorption Edge of TISe Under Hydrostatic Pressure. Physica Status Solidi (B): Basic Research, 1982, 113, K127.	1.5	6
35	Thermal hysteresis and memory effects in TlGaSe2crystal with incommensurate phase. Phase Transitions, 2005, 78, 413-419.	1.3	6
36	Phase transitions in the system of TlGaxln1â^'xSe2xS2(1â^'x) solutions under hydrostatic pressure. Solid State Communications, 1985, 56, 989-993.	1.9	5

#	Article	IF	CITATIONS
37	Electrical and pyroelectric properties of TIInS2. Ferroelectrics, 1988, 83, 161-164.	0.6	5
38	Effect of lattice deformation and phase transitions on the electronic spectra of TlGaS2, TlGaSe2, and TllnS2 layered semiconductors. Physics of the Solid State, 2003, 45, 2242-2248.	0.6	5
39	Photovoltaic currents and activity of structural defects in a ferroelectric–semiconductor TllnS2: La single crystal. Physics of the Solid State, 2016, 58, 716-722.	0.6	5
40	Magnetodielectric effects in Co-implanted TllnS <sub>2</sub> and TlGaSe <sub>2</sub> crystals. Phase Transitions, 2016, 89, 568-577.	1.3	5
41	EPR study of Fe3+centers in ternary layered TllnS2 single crystal. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 3567-3570.	0.8	4
42	Parametric resonance and photogalvanic currents in layered TlGaSe2 crystals. Physics of the Solid State, 2017, 59, 457-462.	0.6	4
43	xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si7.svg"> <mml:mrow><mml:mi mathvariant="normal"&gt;T<mml:mi mathvariant="normal"&gt;I<mml:msub><mml:mrow><mml:mi mathvariant="normal"&gt;I<mml:mi< td=""><td>2.3</td><td>3</td></mml:mi<></mml:mi </mml:mrow></mml:msub></mml:mi </mml:mi </mml:mrow>	2.3	3
44	mathvariant="normal">n <mmkmrow><mmkmn> 1</mmkmn><mmkmo><td>nml:mi&gt;x&lt;</td><td>:/mml:mi&gt;1</td></mmkmo></mmkmrow>	nml:mi>x<	:/mml:mi>1
45	Phase Relations and Properties of Phases in the TlGaSe2–TlCoSe2 System. Inorganic Materials, 2003, 39, 680-682.	0.8	0
46	Admittance and Permittivity in Doped Layered TlGaSe_2 Single Crystals. Acta Physica Polonica A, 2014, 125, 1267-1271.	0.5	0
47	T–x phase diagram and electrical conductivity of solid solutions in the TlInSe2–TlGaTe2 system. Inorganic Materials, 2015, 51, 877-883.	0.8	O